

REMARKS/ARGUMENTS

Favorable reconsideration of this application as presently amended and in light of the following discussion is requested.

Claims 13 and 16-23 are pending in the present application. Claims 13, 16, and 21 are amended and Claims 14, 15, and 24 are canceled without prejudice by the present amendment.

In the outstanding Office Action, Claims 14 and 24 were withdrawn from consideration and Claims 13 and 15-23 were rejected under 35 U.S.C. § 102(b) as anticipated by Jaso et al. (U.S. Patent No. 5,894,152, herein "Jaso").

Regarding the rejection of Claims 13 and 15-23 under 35 U.S.C. § 102(b) as anticipated by Jaso, independent Claim 13 has been amended to recite that "each of said plurality of first semiconductor layers is surrounded by said second semiconductor layer." The claim amendment finds support in Figure 7 and its corresponding description in the specification and in Claim 15, now cancelled. Independent Claim 21 is amended to recite that a first semiconductor layer has "a shape different than a rectangle," and a second semiconductor layer has "a rectangular portion, and said rectangular portion of said second semiconductor layer and said first semiconductor layer having together the shape of a rectangle." The claim amendments find support in Figure 9 and its corresponding description in the specification. No new matter is believed to be added.

Briefly recapitulating, amended Claim 13 is directed to a semiconductor device that includes a plurality of first semiconductor layers formed in a first region of a semiconductor substrate and a second semiconductor layer formed in a second region of the semiconductor substrate. The plurality of first semiconductor layers is formed with one of an insulating film and a cavity interposed between the semiconductor substrate and the plurality of the first

semiconductor layers. Each of the plurality of the first semiconductor layers is surrounded by the second semiconductor layer.

In a non-limiting example, Figure 7 shows the substrate 31, the plurality of first semiconductor layers 32, and the second semiconductor layer 33. Figure 7 also shows that each of the first semiconductor layer 32 is surrounded by the second semiconductor layer 33.

Turning to the applied art, Jaso shows in Figures 5 and 6 a bulk area 102, and SOI areas 100 and 104 such that the SOI area 100 is surrounded by the bulk area 102 but the SOI area 104 is not surrounded by the bulk area 102. Jaso specifically discloses at column 4, lines 33-37, that “an area **100** of SOI is completely surrounded by a bulk area **102**, which is in turn completely surrounded by areas of SOI **104**.”

Further, Jaso shows in Figure 6 a SOI region 120 and a bulk region 122. The SOI region 120 includes an insulation layer 14 formed between a substrate 12 and a semiconductor layer 16 and the bulk region 122 includes a P-type epi layer 30 also formed on the substrate 12. The outstanding Office Action asserts at page 2, last two paragraphs, that the semiconductor layer 16 and the SOI areas 100 and 104 of Jaso correspond to the claimed plurality of first semiconductor layers and the bulk areas 102 and 122 of Jaso correspond to the claimed second semiconductor layer.

However, Jaso does not teach or suggest that each of the plurality of first semiconductor layers is surrounded by a second semiconductor layer. In other words, Jaso does not teach or suggest that the first SOI layer 104 is surrounded by the bulk area 102, as required by amended Claim 13.

Accordingly, it is respectfully submitted that independent Claim 13 and each of the claims depending therefrom patentably distinguish over Jaso.

Regarding independent Claim 21, Figure 9 shows a first semiconductor layer 32 that has a shape different than a rectangle, and a second semiconductor layer having a rim portion 33 and a rectangular portion 33A. The rim portion 33 is formed on a semiconductor substrate 31 and surrounds the first semiconductor layer 32. The rectangular portion 33A has together with the first semiconductor layer 32 the shape of a rectangle.

However, Jaso does not teach or suggest that a first semiconductor layer has a shape different than a rectangle, and a rectangular portion of a second semiconductor layer and the first semiconductor layer have together the shape of a rectangle. On the contrary, Jaso shows in Figure 5 that the first semiconductor layer 100 has the shape of a rectangle.

Accordingly, it is respectfully submitted that independent Claim 21 and each of the claims depending therefrom patentably distinguish over Jaso.

Consequently, in light of the above discussion and in view of the present amendment, the present application is believed to be in condition for allowance and an early and favorable action to that effect is respectfully requested.

Respectfully submitted,

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